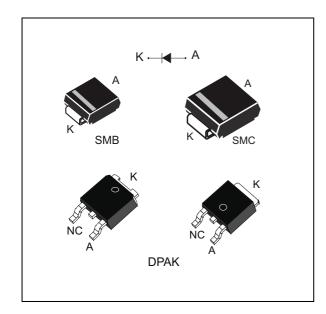




Ultrafast recovery diode

Datasheet - production data



Description

The STTH4R02 uses ST's new 200 V planar Pt doping technology, and it is specially suited for switching mode base drive and transistor circuits.

Packaged in DPAK, SMB and SMC, this device is intended for use in low voltage, high frequency inverters, freewheeling and polarity protection.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	4 A
V_{RRM}	200 V
V _F (typ)	0.76 V
T _j (max)	175 °C
t _{rr} (typ)	16 ns

Features

- · Negligible switching losses
- High junction temperature
- Very low conduction losses

This is information on a product in full production.

- Low forward and reverse recovery times
- ECOPACK[®]2 compliant component for DPAK on demand

Characteristics STTH4R02

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parar	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage			200	V
	Forward rms current	DPAK		10	Α
I _F (RMS)	Polward fills current	SMB / SMC		70	
1	Average forward current,	DPAK	T _c = 160 °C	4	Α
I _{F(AV)}	δ = 0.5, square wave	SMB / SMC	T _L = 95 °C	4	A
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			70	А
T _{stg}	Storage temperature range			-65 to +175	°C
T _j	Maximum operating junction temperature			175	°C

Table 3. Thermal parameters

Symbol	Parameter	Max. value	Unit	
R _{th(j-c)}	Junction to case	DPAK	3.5	°C/W
R _{th(j-l)}	Junction to lead	SMB / SMC	20	C/VV

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	\/- - \/	-		3	пΛ
'R'	Reverse leakage current	T _j = 125 °C	$V_R = V_{RRM}$	ı	2	20	μA
		T _i = 25 °C	I _F = 12 A	-	1.15	1.25	
V _F ⁽²⁾	(2) Forward voltage drop	,	1 – 4 A	-	0.95	1.05	V
		T _j = 150 °C	I _F = 4 A	-	0.76	0.83	

^{1.} Pulse test: t_p = 5 ms, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 0.67 \times I_{F(AV)} + 0.04 \times I_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

STTH4R02 Characteristics

Table 5. Dynamic electrical characteristics

Symbol	Parameter		Tests conditions	Min.	Тур.	Max.	Unit
	Reverse recovery time	T = 25 °C	$I_F = 1 \text{ A}$ $dI_F/dt = -50 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$	-	24	30	ns
t _{rr}	Reverse recovery time		$I_F = 1 \text{ A}$ $dI_F/dt = -100 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$	-	16	20	115
I _{RM}	Reverse recovery current	T _j = 125 °C	$I_F = 4 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	4.4	5.5	Α
t _{fr}	Forward recovery time	T _j = 25 °C	$I_F = 4 \text{ A}$ $dI_F/dt = 50 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$	-	80		ns
V _{FP}	Forward recovery voltage	•	I _F = 4 A dI _F /dt = 50 A/μs	-	1.6		V



Characteristics STTH4R02

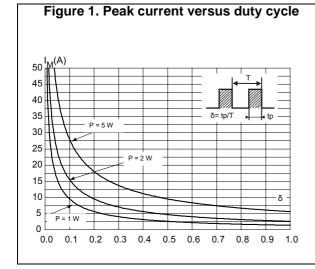


Figure 2. Forward voltage drop versus forward current (typical values) $I_{\mathsf{F}}(\mathsf{A})$ 100 75 T = 150 °C 50 25 0 1.0 3.5 0.5 1.5 2.0 2.5 3.0 0.0

Figure 3. Forward voltage drop versus forward current (maximum values)

1.5

Figure 5. Relative variation of thermal

impedance, junction to ambient, versus pulse

2.0

2.5

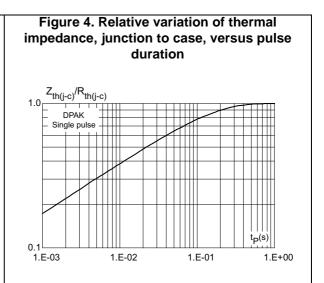
3.0

3.5

0.0

0.5

1.0



duration (SMB) $Z_{th(j-a)}/R_{th(j-a)}$ 1.0 0.9 SMB $S_{CU} = 1 \text{ cm}^2$ 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 0.0 1.E+02 1.E-01 1.E+00 1.E+01 1.E+03

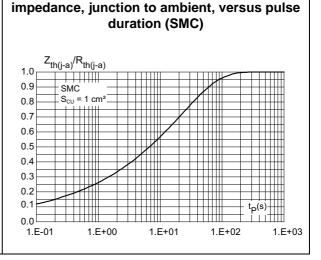


Figure 6. Relative variation of thermal

STTH4R02 **Characteristics**

1000

Figure 7. Junction capacitance versus reverse applied voltage (typical values) 100 C(pF) $V_{R}(V)$

Figure 8. Reverse recovery charges versus dl_F/dt (typical values) $Q_{rr}(nC)$ 100 80 60 40 20 $dI_F/dt (A/\mu s)$ 0 0 100 150 200 250 300 350 400 450 500

Figure 9. Reverse recovery time versus dl_F/dt (typical values) t_{rr}(ns) 80 70 60 50 40 30 20 10 dl_F/dt (A/μs) 0 10 100 1000

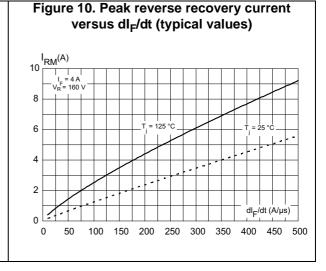
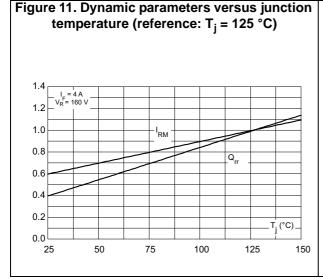
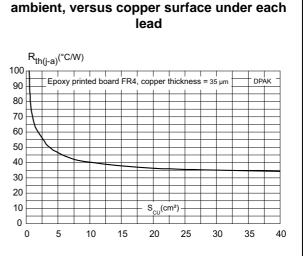


Figure 12. Thermal resistance, junction to





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Characteristics STTH4R02

Figure 13. Thermal resistance, junction to ambient, versus copper surface under each lead

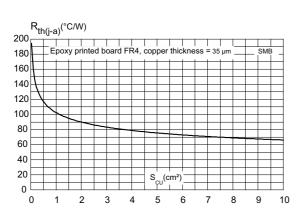
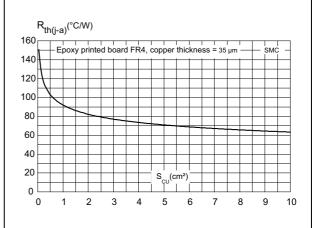


Figure 14. Thermal resistance, junction to ambient, versus copper surface under tab



2 **Package information**

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Band indicates cathode

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DPAK package information 2.1

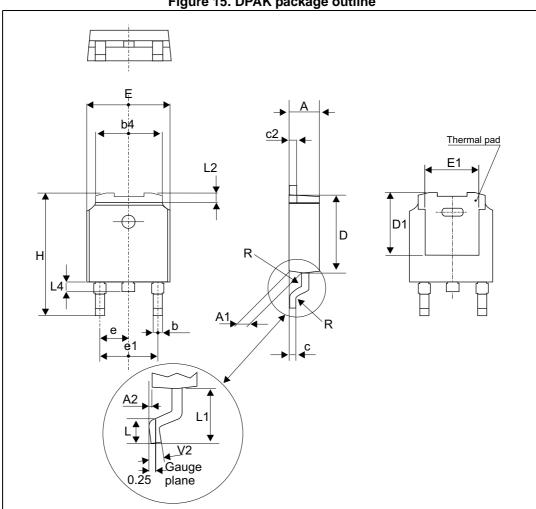


Figure 15. DPAK package outline

Note:

This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

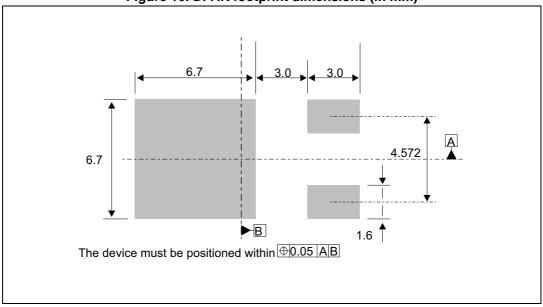


Package information STTH4R02

Table 6. DPAK package mechanical data

			· ·	Dimensions		
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	2.18		2.40	0.085		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	4.95		5.46	0.194		0.214
С	0.46		0.61	0.018		0.024
c2	0.46		0.60	0.018		0.023
D	5.97		6.22	0.235		0.244
D1	4.95		5.60	0.194		0.220
Е	6.35		6.73	0.250		0.264
E1	4.32		5.50	0.170		0.216
е		2.28			0.090	
e1	4.40		4.70	0.173		0.185
Н	9.35		10.40	0.368		0.409
L	1.00		1.78	0.039		0.070
L2			1.27			0.050
L4	0.60		1.02	0.023		0.040
V2	-8°		+8°	-8°		8°

Figure 16. DPAK footprint dimensions (in mm)



STTH4R02 Package information

2.2 SMB package information

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Figure 17. SMB package outline

Table 7. SMB package mechanical data

	Dimensions				
Ref.	Millim	lillimeters Inc		hes	
	Min.	Max.	Min.	Max.	
A1	1.90	2.45	0.075	0.096	
A2	0.05	0.20	0.002	0.008	
b	1.95	2.20	0.077	0.087	
С	0.15	0.40	0.006	0.016	
D	3.30	3.95	0.130	0.156	
E	5.10	5.60	0.201	0.220	
E1	4.05	4.60	0.159	0.181	
L	0.75	1.50	0.030	0.059	

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Package information STTH4R02

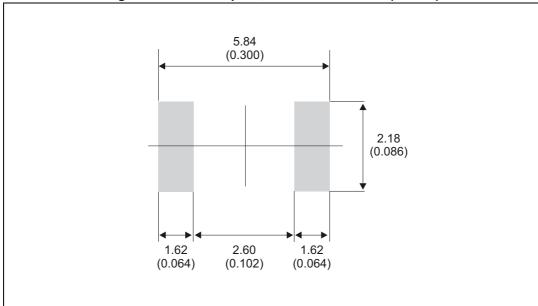


Figure 18. SMB footprint, dimensions in mm (inches)

STTH4R02 Package information

2.3 SMC package information

Figure 19. SMC package outline

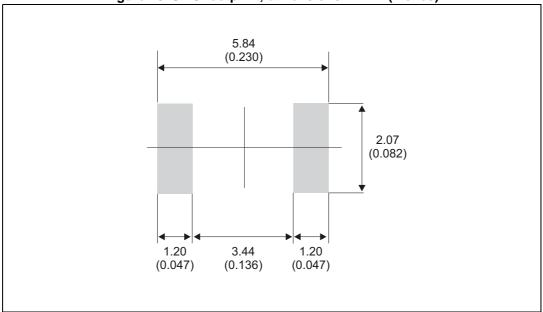
Package information STTH4R02

Table 8. SMC package mechanical data

	Dimensions				
Ref.	Millim	eters	Inc	hes	
	Min.	Max.	Min.	Max.	
A1	1.90	2.45	0.075	0.096	
A2	0.05	0.20	0.002	0.008	
b ⁽¹⁾	2.90	3.20	0.114	0.126	
c ⁽¹⁾	0.15	0.40	0.006	0.016	
D	5.55	6.25	0.218	0.246	
E	7.75	8.15	0.305	0.321	
E1	6.60	7.15	0.260	0.281	
E2	4.40	4.70	0.173	0.185	
L	0.75	1.50	0.030	0.059	

^{1.} Dimensions b and c apply to plated leads

Figure 20. SMC footprint, dimensions in mm (inches)



3 Ordering information

STTH4R02

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH4R02B-TR	STTH 4R02	DPAK	0.32 g	2500	Tape and reel
STTH4R02U	4R2U	SMB	0.110 g	2500	Tape and reel
STTH4R02S	4R2S	SMC	0.243 g	2500	Tape and reel

4 Revision history

Table 10. Document revision history

Date	Revision	Changes
03-May-2006	1	First issue.
10-Oct-2006	2	Added SMC package
13-Apr-2010	3	Updated ECOPACK statement. Updated dimensions tables for SMB and SMC.
01-Jul-2010	4	Separated junction to lead values from junction to case values in <i>Table 3</i> .
20-Nov-2014	5	Removed TO-220AC, TO-220FPAC and DO-201AB package informations.
02-Nov-2016	6	Updated DPAK package information and reformatted to current standard.

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